

# 2.7 inch E-paper Display Series

**WAA0270A2AAA7NXXX000** 



## **Product Specifications**

Customer	Standard
Description	2.7" E-PAPER DISPLAY
Model Name	WAA0270A2AAA7NXXX000
Date	2025/02/12
Revision	1.0

	Design Engineering  Approval Check Design				



### **REVISION HISTORY**

Rev	Date	Item	Page	Remark
1.0	02.12.2025	New Creation	ALL	



### **CONTENTS**

1.	Over View	6
2.	Features	6
3.	Mechanical Specification	6
4.	Mechanical Drawing of EPD Module	7
5.	Input/output Pin Assignment	8
6.	Electrical Characteristics	9
	6.1 Absolute Maximum Rating	9
	6.2 Panel DC Characteristics	
	6.3 Panel AC Characteristics	11
	6.3.1 MCU Interface Selection	11
	6.3.2 MCU Serial Interface (4-wire SPI)	11
	6.3.3 MCU Serial Interface (3-wire SPI)	12
	6.3.4 Interface Timing	13
7.	Command Table	14
8.	Optical Specification	27
9.	Handling, Safety, and Environment Requirements	28
10	Reliability Test	20



11.	Block Diagram	30
12.	Reference Circuit	31
13.	Matched Development Kit	32
14.	Typical Operating Sequence	33
	14.1 Normal Operation Flow	33
15.	Inspection condition	34
	15.1 Environment	34
	15.2 Illuminance	34
	15.3 Inspect method	34
	15.4 Display area	34
	15.5 Inspection standard	35
	15.5.1 Electric inspection standard	35
	15.5.2 Appearance inspection standard	36
16.	. Packaging	.38
17.	Precautions	.39

2.7 inch Series



#### 1. Over View

WAA0270A2AAA7NXXX000 is an Active Matrix Electrophoretic Display (AM EPD), with front light panel. The display is capable to display image at 1-bit white, black full display capabilities. The 2.7inch active area contains 264×176pixels. The module is a TFT-array driving electrophoresis display, with integrated circuits including gate driver, source driver, MCU interface, timing controller, oscillator, DC-DC, SRAM, LUT, VCOM. Module can be used in portable electronic devices, such as Electronic Shelf Label (ESL) System.

#### 2.Features

264×176 pixels display
High contrast
High reflectance
Ultra wide viewing angle Ultra low power consumptionPure
reflective mode
Bi-stable display
Commercial temperature range
Landscape portrait modes
Hard-coat antiglare display surface
Ultra Low current deep sleep mode
On chip display RAM
Waveform can stored in On-chip OTP or written by MCU

With front light panel, 4 LEDs in serial, operating voltage: 12V

On-chip oscillator
On-chip booster and regulator control for generating VCOM, Gate and Source driving voltage
I2C signal master interface to read external temperature sensor Built-in temperature sensor

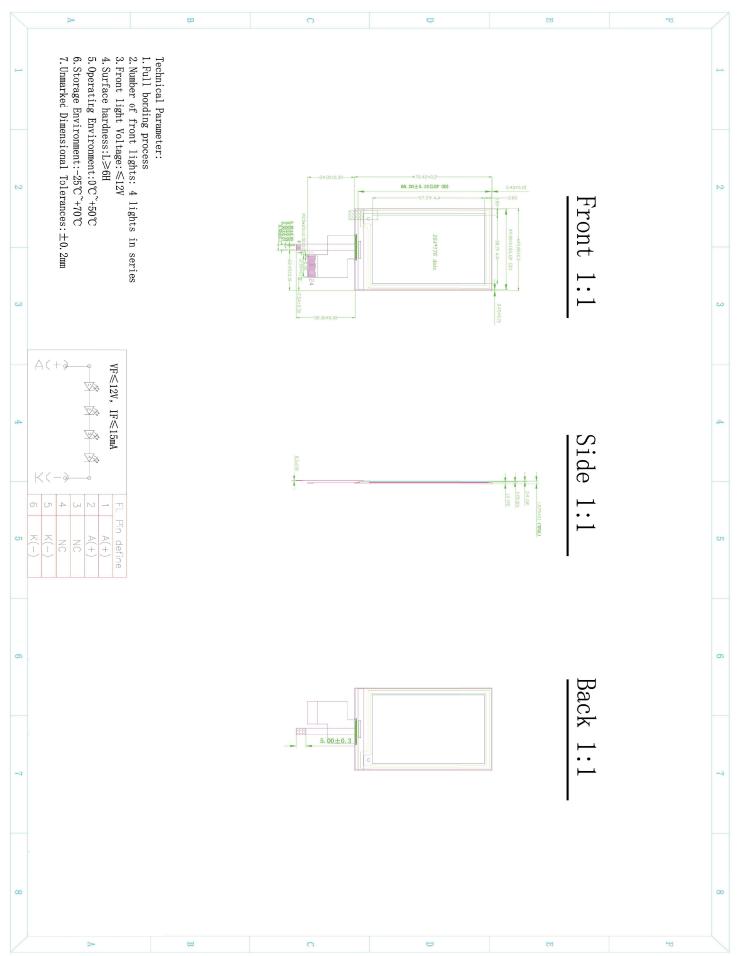
### 3. Mechanical Specifications

Serial peripheral interface available

Parameter	Specifications	Unit	Remark
Screen Size	2.7	Inch	
Display Resolution	264(H)×176(V)	Pixel	Dpi:117
Active Area	38.19×57.29	mm	
Pixel Pitch	0.217×0.217	mm	
Pixel Configuration	Rectangle		
Outline Dimension	45.8 (H)×70.42(V) ×1.58(D)	mm	
Weight	8.84±0.5	g	



### 4. Mechanical Drawing of EPD module





### 5. Input /Output Pin Assignment

No.	Name	I/O	Description	Remark
1	NC		Do not connect with other NC pins	Keep Open
2	GDR	О	N-Channel MOSFET Gate Drive Control	
3	RESE	I	Current Sense Input for the Control Loop	
4	NC	NC	Do not connect with other NC pins	Keep Open
5	VSH2	С	Positive Source driving voltage(Red)	
6	TSCL	О	I <sup>2</sup> C Interface to digital temperature sensor Clock pin	
7	TSDA	I/O	I <sup>2</sup> C Interface to digital temperature sensor Data pin	
8	BS1	I	Bus Interface selection pin	Note 5-5
9	BUSY	О	Busy state output pin	Note 5-4
10	RES#	I	Reset signal input. Active Low.	Note 5-3
11	D/C#	I	Data /Command control pin	Note 5-2
12	CS#	I	Chip select input pin	Note 5-1
13	SCL	I	Serial Clock pin (SPI)	
14	SDA	I	Serial Data pin (SPI)	
15	VDDIO	P	Power Supply for interface logic pins It should be connected with VCI	
16	VCI	P	Power Supply for the chip	
17	VSS	P	Ground	
18	VDD	С	Core logic power pin VDD can be regulated internally from VCI. A capacitor should be connected between VDD and VSS	
19	VPP	P	FOR TEST	
20	VSH1	С	Positive Source driving voltage	
21	VGH	С	Power Supply pin for Positive Gate driving voltage and VSH1	
22	VSL	С	Negative Source driving voltage	
23	VGL	С	Power Supply pin for Negative Gate driving voltage VCOM and VSL	
24	VCOM	С	VCOM driving voltage	



I = Input Pin, O = Output Pin, I/O = Bi-directional Pin (Input/output), P = Power Pin, C = Capacitor Pin

**Note 5-1:** This pin (CS#) is the chip select input connecting to the MCU. The chip is enabled for MCU communication only when CS# is pulled LOW.

**Note 5-2:** This pin is (D/C#) Data/Command control pin connecting to the MCU in 4-wire SPI mode. When the pin is pulled HIGH, the data at SDA will be interpreted as data. When the pin is pulled LOW, the data at SDA will be interpreted as command.

Note 5-3: This pin (RES#) is reset signal input. The Reset is active low.

**Note 5-4:** This pin is Busy state output pin. When Busy is High, the operation of chip should not be interrupted, command should not be sent. The chip would put Busy pin High when –Outputting display waveform -Communicating with digital temperature sensor

**Note 5-5:** Bus interface selection pin

BS1 State	MCU Interface
L	4-lines serial peripheral interface(SPI) - 8 bits SPI
Н	3- lines serial peripheral interface(SPI) - 9 bits SPI

# 6. Electrical Characteristics6.1 Absolute Maximum Rating

Parameter	Symbol	Rating	Unit
Logic supply voltage	VCI	-0.5 to +6.0	V
Logic Input voltage	VIN	-0.5 to VCI +0.5	V
Logic Output voltage	VOUT	-0.5 to VCI +0.5	V
Operating Temp range	TOPR	0 to +50	° C
Storage Temp range	TSTG	-25 to+70	° C
Optimal Storage Humidity	HSTGo	55±10	%RH

#### Note:

Maximum ratings are those values beyond which damages to the device may occur. Functional operation should be restricted to the limits in the Panel DC Characteristics tables.

#### 6.2 Panel DC Characteristics

The following specifications apply for: VSS=0V, VCI=3.0V, TOPR =25°C.

WINSTAR Display 9/39 2.7 inch Series



Parameter	Symbol	Conditions	Applica ble pin	Min.	Typ.	Max	Units
Single ground	V <sub>SS</sub>			-	0	-	V
Logic supply voltage	$V_{\rm CI}$		VCI	2.2	3.0	3.7	V
Core logic voltage	$V_{ m DD}$		VDD	1.7	1.8	1.9	V
High level input voltage	$V_{\mathrm{IH}}$	-		0.8 V <sub>CI</sub>	-	-	V
Low level input voltage	V <sub>IL</sub>	-		-	-	0.2 V <sub>CI</sub>	V
High level output voltage	V <sub>OH</sub>	IOH = - 100uA		0.9 VCI	-	-	V
Low level output voltage	V <sub>OL</sub>	IOL = 100uA			-	$0.1~\mathrm{V_{CI}}$	V
Typical power	P <sub>TYP</sub>	$V_{CI} = 3.0 V$			9		mW
Deep sleep mode	P <sub>STPY</sub>	$V_{CI} = 3.0 V$			0.003		mW
Typical operating current	Iopr_V <sub>CI</sub>	$V_{CI} = 3.0 V$		-	3		mA
Full update time		25 °C			3		sec
Fast update time	-	25 °C			1.5		sec
Partial update time		25 °C			0.42		sec
Sleep mode current	Islp_V <sub>CI</sub>	DC/ DC off  No clock  No input load  Ram data retain	-	-	20		uA
Deep sleep mode current	Idslp_V <sub>CI</sub>	DC/ DC off  No clock  No input load  Ram data not retain	-	-	1	5	uA

#### Notes:

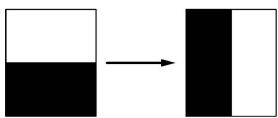
- 1) Refresh time: the time it takes for the whole process from the screen change to the screen stabilization.
- 2) The difference between different refresh methods:

Full refresh: The screen will flicker several times during the refresh process;

Fast Refresh: The screen will flash once during the refresh process; Partial refresh: The screen does not flicker during the refresh process.

During the fast refresh or partial refresh of the electronic paper, it is recommended to add a full-screen refresh after 5 consecutive operations to reduce the accumulation of afterimages on the screen.

- 1. The typical power is measured with following transition from horizontal 2 scale pattern to vertical 2 scale pattern.
- 2. The deep sleep power is the consumed power when the panel controller is in deep sleep mode.
- 3. The listed electrical/optical characteristics are only guaranteed under the controller & waveform provided by WINSTAR DISPLAY.





#### 6.3 Panel AC Characteristics

#### 6.3.1 MCU Interface Selection

MCU interface is pin selectable by BS1 shown in Table 6-1.

Table 6-1: Interface pins assignment under different MCU interface

	Pin Name					
MCU Interface	BS1	RES#	CS#	D/C#	SCL	SDA
4-wire serial peripheral interface (SPI)	L	RES#	CS#	DC#	SCL	SDA
3-wire serial peripheral interface (SPI) – 9 bits SPI	Н	RES#	CS#	L	SCL	SDA

Note: (1) L is connected to VSS and H is connected to VDDIO

#### 6.3.2 MCU Serial Interface (4-wire SPI)

The 4-wire SPI consists of serial clock SCL, serial data SDA, D/C# and CS#. The control pins status in 4-wire SPI in writing command/data is shown in Table 6-2 and the write procedure 4-wire SPI is shown in Table 6-2

Table 6-2: Control pins status of 4-wire SPI

Function	SCL pin	SDA pin	D/C# pin	CS# pin
Write command	1	Command bit	L	L
Write data	1	Data bit	Н	L

Note:(1) L is connected to VSS and H is connected to VDDIO

- (2) ↑ stands for rising edge of signal
- (3) SDA (Write Mode) is shifted into an 8-bit shift register on every rising edge of SCL in the order of D7, D6, ... D0. The level of D/C# should be kept over the whole byte. The data byte in the shift register is written to the Graphic Display Data RAM (RAM)/Data Byte register or command Byte register according to D/C# pin.

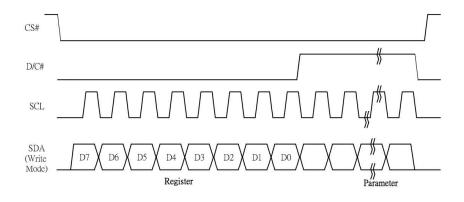


Figure 6-1: Write procedure in 4-wire SPI mode

In the read operation (Command 0x1B, 0x27, 0x2D, 0x2E, 0x2F, 0x35). After CS # is pulled low, the first byte sent is command byte, D/C# is pulled low. After com mand byte sent, the following byte(s) read are data byte(s), so D/C# bit is then pulled high. An 8-bit data will be shifted out on every clock falling edge. The serial data SDA bit shifting sequence is D7, D6, to D0 bit. Figure 6-2 shows the read procedure in 4-wire SPI.



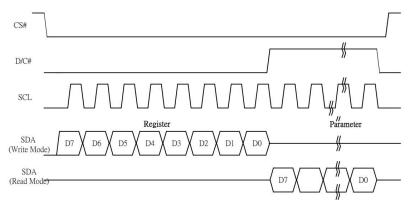


Figure 6-2: Read procedure in 4-wire SPI mode

### 6.3.3 MCU Serial Interface (3-wire SPI)

The 3-wire SPI consists of serial clock SCL, serial data SDA and CS#. The operation is similar to 4-wire SPI while D/C# pin is not used and it must be tied to LOW. The control pins status in 3-wire SPI is shown in Table 6-3.

In the write operation, a 9-bit data will be shifted into the shift register on every clock rising edge. The bit shifting sequence is D/C# bit, D7 bit, D6 bit to D0 bit. The first bit is D/C# bit which determines the following byte is command or data. When D/C# bit is 0, the following byte is command. When D/C# bit is 1, the following byte is data. Table 6-3 shows the write procedure in 3-wire SPI

 Function
 SCL pin
 SDA pin
 D/C# pin
 CS# pin

 Write command
 ↑
 Command bit
 Tie LOW
 L

 Write data
 ↑
 Data bit
 Tie LOW
 L

Table 6-3: Control pins status of 3-wire SPI

Note: (1) L is connected to VSS and H is connected to VDDIO

(2) ↑ stands for rising edge of signal

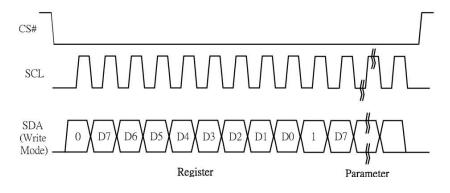


Figure 6-3: Write procedure in 3-wire SPI

In the read operation (Register 0x1B, 0x27, 0x2D, 0x2E, 0x2F, 0x35). SDA data are transferred in the unit of 9 bits. After CS# pull low, the first byte is command by te, the D/C# bit is as 0 and following with the register byte. After command byte send, the following byte(s) are data byte(s), with D/C# bit is 1.After D/C# bit sending from MCU, an 8-bit data will be shifted out on every clock falling edge. The serial data SDA bit shifting sequence is D7, D6, to D0 bit. Figure 6-4 shows the read procedure in 3-wire SPI.



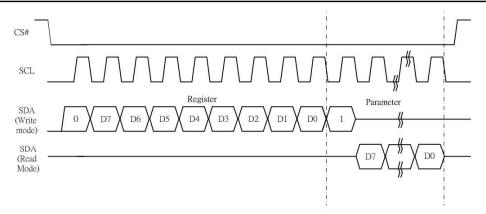


Figure 6-4: Read procedure in 3-wire SPI mode

### **6.3.4 Interface Timing**

The following specifications apply for: VDDIO - VSS = 2.2V to 3.7V, CL=20pF

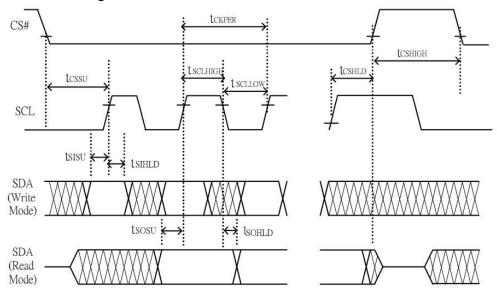
#### Write mode

Symbol	Parameter	Min	Тур	Max	Unit
f <sub>SCL</sub>	SCL frequency (Write Mode)		-	20	MHz
tcssu	Time CS# has to be low before the first rising edge of SCLK	60	120	(2)	ns
tcshld	Time CS# has to remain low after the last falling edge of SCLK	65	(-)	-	ns
tcsнigh	Time CS# has to remain high between two transfers	100	(=)	(-)	ns
tsclhigh	Part of the clock period where SCL has to remain high	25	-		ns
tscllow	Part of the clock period where SCL has to remain low	25	-	-	ns
tsisu	Time SI (SDA Write Mode) has to be stable before the next rising edge of SCL	10	(=)	-	ns
tsiHLD	Time SI (SDA Write Mode) has to remain stable after the rising edge of SCL	40	720	121	ns

#### Read mode

Symbol	Parameter	Min	Тур	Max	Unit
fscL	SCL frequency (Read Mode)	1 4	-	2.5	MHz
tcssu	Time CS# has to be low before the first rising edge of SCLK	100	( <del>(*</del> )	-	ns
tcshld	Time CS# has to remain low after the last falling edge of SCLK	50	-	-	ns
tcsнigh	Time CS# has to remain high between two transfers	250			ns
tsclhigh	Part of the clock period where SCL has to remain high	180	-	-	ns
tscllow	Part of the clock period where SCL has to remain low	180	878	87	ns
tsosu	Time SO(SDA Read Mode) will be stable before the next rising edge of SCL	-	50	1(4)	ns
tsohld	Time SO (SDA Read Mode) will remain stable after the falling edge of SCL	-	0	0-	ns

Note: All timings are based on 20% to 80% of VDDIO-VSS





### 7. Command Table

	BELLION STREET	d Ta		De	DE	D4	D2	D2	D4	DA	Command	Docorinti			
INER.				D6	D5	D4	D3	D2	D1	D0	Command	Description			
0	0	01	0	0	0	0	0	0	0	1	Driver Output control	Gate settir		1 206 MIL	<b>v</b>
0	1		A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>		A[8:0]= 12 MUX Gate			
0	1		0	0	0	0	0	0	0	A <sub>8</sub>		MOX Out	111100 00	unig do (i t	[0.0]
0	1		0	0	0	0	0	B <sub>2</sub>	B <sub>1</sub>	Bo	Bo	B [2:0] = 0 Gate scan  B[2]: GD Selects the GD=0 [PC G0 is the output sec GD=1, G1 is the output sec SM=0 [PC G0, G1, G interlaced; SM=1, G0, G2, G	e 1st outport, and the sequence is canning control of the sequence is canning the sequence is canni	out Gate output char G0,G1, G output char G1, G0, C	nnel, gate i2, G3, nnel, gate i3, G2, te driver.
												B[0]: TB TB = 0 [P0 TB = 1, sc	OR], scar	from G0	to G295
0	0	03	0	0	0	0	0	0	1	1	Gate Driving voltage	B[0]: TB TB = 0 [P0 TB = 1, sc	OR], scar	n from G0 G295 to G	to G295
C	0	03	0 0	0 0	0 0	0 A <sub>4</sub>	0 A <sub>3</sub>	0 A <sub>2</sub>	1 A <sub>1</sub>	1 A <sub>0</sub>	Gate Driving voltage Control	B[0]: TB TB = 0 [P0 TB = 1, so Set Gate 0 A[4:0] = 00	OR], scar can from o driving vo Oh [POR]	n from G0 G295 to G	to G295 0.
61111	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, so	OR], scar can from o driving vo Oh [POR]	n from G0 G295 to G	to G295 0.
61111	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc Set Gate 0 A[4:0] = 00 VGH settin	OR], scar can from 0 driving vo 0h [POR] ng from 1	of from G0 G295 to G oltage	to G295 0.
6,34	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc Set Gate of A[4:0] = 00 VGH settin A[4:0]	OR], scar can from o driving vo 0h [POR] ng from 1 VGH	n from G0 G295 to G oltage 0V to 20V A[4:0]	to G295 0.
6,34	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc  Set Gate of A[4:0] = 00 VGH settin A[4:0] 00h	OR], scar can from 0 driving vo 0h [POR] ng from 1 VGH 20	of from G0 G295 to G oltage OV to 20V A[4:0] ODh	to G295 0. VGH
61111	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc  Set Gate of A[4:0] = 00 VGH settin A[4:0]	OR], scar can from 0 driving vo 0h [POR] ng from 1 VGH 20 10	of from G0 G295 to G oltage OV to 20V A[4:0] ODh OEh	vGH 15 15.5
C	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc  Set Gate of A[4:0] = 00 VGH settin A[4:0] 00h 03h 04h	OR], scar can from 0 driving vo 0h [POR] ng from 1 VGH 20 10 10.5	of from G0 G295 to G oltage OV to 20V A[4:0] ODh OEh OFh	VGH 15 15.5
C.S.	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, so  Set Gate of A[4:0] = 00 VGH settin A[4:0] 00h 03h 04h 05h	OR], scar can from 0 driving vo 0h [POR] ng from 1 VGH 20 10 10.5	of from G0 G295 to G oltage OV to 20V A[4:0] ODh OEh OFh	VGH 15 15.5 16 16.5
6,34	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc  Set Gate of A[4:0] = 00 VGH settin A[4:0] 00h 03h 04h 05h 06h 07h	OR], scar can from 0 oh [POR] ng from 1 VGH 20 10 10.5 11 11.5	of from G0 G295 to G  Oltage  OV to 20V  A[4:0]  ODh  OEh  OFh  10h  11h  12h	VGH 15 15.5 16 16.5 17
6,34	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0] TB = 1, so  Set Gate of A[4:0] = 00 VGH settin  A[4:0] 00h 03h 04h 05h 06h 07h 08h	OR], scar can from 0 driving vo 0h [POR] ng from 1 VGH 20 10 10.5 11 11.5 12	of from G0 G295 to G  Oltage  OV to 20V  A[4:0]  ODh  OEh  OFh  10h  11h  12h  13h	VGH 15 15.5 16 16.5 17 17.5
Co. Sec.	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc  Set Gate of A[4:0] = 00 VGH settin  A[4:0] = 00 00h 03h 04h 05h 06h 07h 08h 07h	OR], scar can from 0 oh [POR] ng from 1 VGH 20 10 10.5 11 11.5 12 12.5	of from G0 G295 to G  litage  OV to 20V  A[4:0]  ODh  OEh  OFh  10h  11h  12h  13h  14h	VGH 15 15.5 16 16.5 17 17.5 18
61111	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc  Set Gate of A[4:0] = 00 VGH settin  A[4:0] 00h 03h 04h 05h 06h 07h 08h 07h 08h	OR], scar can from 0 oh [POR] ng from 1 VGH 20 10 10.5 11 11.5 12 12.5 12	of from G0 G295 to G  Soltage  OV to 20V  A[4:0]  ODh  OEh  OFh  10h  11h  12h  13h  14h  15h	VGH 15 15.5 16 16.5 17 17.5 18 18.5
0 0	. 30	03	100	1982	S. Jane	100	200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, so  Set Gate of A[4:0] = 00 VGH settin  A[4:0] 00h 03h 04h 05h 06h 07h 08h 07h 08h 09h	OR], scar can from 0 oh [POR] ng from 1 VGH 20 10 10.5 11 11.5 12 12.5 12	of from G0 G295 to G  litage  OV to 20V  A[4:0]  ODh  OEh  OFh  10h  11h  12h  13h  14h  15h  16h	VGH 15 15.5 16 16.5 17 17.5 18 18.5 19
C	. 30	03	100	1982	S. Jane		200		-	0.0		B[0]: TB TB = 0 [P0 TB = 1, sc  Set Gate of A[4:0] = 00 VGH settin  A[4:0] 00h 03h 04h 05h 06h 07h 08h 07h 08h	OR], scar can from 0 oh [POR] ng from 1 VGH 20 10 10.5 11 11.5 12 12.5 12	of from G0 G295 to G  Soltage  OV to 20V  A[4:0]  ODh  OEh  OFh  10h  11h  12h  13h  14h  15h	VGH 15 15.5 16 16.5 17 17.5 18 18.5



W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Comn	nand		Description
0	0	04	0	0	0	0	0	1	0	0	Source	e Driving	voltage	Set Source driving voltage
0	1	N. 2000.00	A7	A <sub>6</sub>	A5	A4	Аз	A <sub>2</sub>	A <sub>1</sub>	Ao	Contro	UI.		A[7:0] = 41h [POR], VSH1 at 15V
)	1		B <sub>7</sub>	B <sub>6</sub>	B <sub>5</sub>	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	Bo				B [7:0] = A8h [POR], VSH2 at 5V.
)	1		C <sub>7</sub>	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	No.	7434	C <sub>1</sub>	Co	-			C[7:0] = 32h [POR], VSL at -15V
			U7	<b>C</b> 6	<b>C</b> 5	<b>U</b> 4	C <sub>3</sub>	C <sub>2</sub>						Remark: VSH1>=VSH2
	]/B[7] H1/VS		oltac	ie se	ttina	from	2.4V	A[	7]/B[7 SH1/\	] = ( /SH2	), Voltag	e settina	from 9V	C[7] = 0, VSL setting from -5V to -17V
	V8.8			,0 00	tui.g				17V		· ronag	o county		TOE SOMING HOME OF NO.
VD4W.	B[7:0]	100 9000	1/VSH2	50.25	3[7:0]	10000	/VSH2		A/B[7:0]	VS	H1/VSH2	A/B[7:0]	VSH1/VSH2	C[7:0] VSL
	8Eh 8Fh		2.4	13 (3)	Fh 10h	. 30	i.7	_	23h 24h	+	9.2	3Ch 3Dh	14.2	0Ah -5
	90h	-	2.6		1h	_	i.9		25h		9.4	3Eh	14.4	0Ch -5.5 0Eh -6
	91h		2.7	-	12h	_	6		26h		9.6	3Fh	14.6	10h -6.5
	92h 93h		2.8		13h 14h	_	.1	3	27h 28h		9.8	40h 41h	14.8	12h -7
	94h		3	9 50	5h	100	1.3		29h		10.2	42h	15.2	14h -7.5
_	95h		3.1	100	6h	377	.4		2Ah	2	10.4	43h	15.4	16h -8
_	96h 97h	_	3.2	1 100	17h 18h	100	i.5	10	2Bh 2Ch		10.6	44h 45h	15.6 15.8	18h -8.5
	98h	_	3.4	25	9h	333	.7	-	2Dh		11	46h	16	1Ah -9 1Ch -9.5
_	99h		3.5	(1)	Ah	-	.8		2Eh		11.2	47h	16.2	1Eh -10
	9Ah 9Bh	-	3.6		Bh Ch	_	7	-	2Fh 30h		11.4	48h 49h	16.4 16.6	20h -10.5
	9Ch		3.8		Dh		.1		31h	1	11.8	4Ah	16.8	22h -11
	9Dh	90	3.9		Eh		.2		32h		12	4Bh	17	24h -11.5
	9Eh		4	C 140	lFh		.3	is-	33h	0	12.2	Other	NA	26h -12 28h -12.5
	9Fh A0h		4.1 4.2	500	Oh Oh	1/5	.4		34h 35h	+	12.4			2Ah -13
_	A1h		4.3		2h		.6		36h	1	12.8			2Ch -13.5
_	A2h	_	4.4	3 797	3h	150	.7		37h		13			2Eh -14
	A3h A4h		4.6 4.6	100	24h		.8	-	38h		13.2			30h -14.5
_	A5h	_	4.7		6h	1.05	.9	15	3Ah	+	13.6			32h -15
	A6h	_	4.8		7h	_	.1	12	3Bh		13.8			34h -15.5
	A7h	-	4.9	_	8h		.2	-		136	71)			36h -16 38h -16.5
	A8h A9h		5.1		9h Ah		.3							3Ah -17
_	AAh	1.	5.2		Bh		.5							Other NA
_	ABh		5.3		Ch	353	.6							
_	ACh ADh		5.4	177	Dh Eh	-	.8							
- 0	AEh		5.6	573	ther	100	IA							
		-		-			7.5							
)	0	08	0	0	0	0	1	0	0	0	Initial	Code Set	ting	Program Initial Code Setting
												rogram	27.0	(54)
														The command required CLKEN=1.
														Refer to Register 0x22 for detail. BUSY pad will output high during
														operation.
_														
)	0	09	0	0	0	0	1	0	0	1			for Initial	Write Register for Initial Code Setting Selection
)	1		A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	Code	Setting		A[7:0] ~ D[7:0]: Reserved
)	1		B <sub>7</sub>	B <sub>6</sub>	B <sub>5</sub>	B <sub>4</sub>	Вз	B <sub>2</sub>	B <sub>1</sub>	B <sub>0</sub>				Details refer to Application Notes of Initi
)	1		C <sub>7</sub>	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	C <sub>3</sub>	C <sub>2</sub>	C <sub>1</sub>	C <sub>0</sub>				Code Setting
)	1		D <sub>7</sub>	D <sub>6</sub>	D <sub>5</sub>	D <sub>4</sub>	D <sub>3</sub>	D <sub>2</sub>	D <sub>1</sub>	D <sub>0</sub>				
)	0	0A	0	0	0	0	1	0	1	0	Read	Register	for Initial	Read Register for Initial Code Setting
S		Un	U	U		0	\$#	U	(8)	U	THE PART OF STREET	Setting	ioi iriitial	Troud Trogister for milital Gode Setting



om /w#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	DO	Command	Description	
0	0	0C	0	0	0	0	1	1	0	0	Booster Soft start	-	with Phase 1, Phase 2 and Phase 3
0	1	00	1	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	A3	A <sub>2</sub>	A <sub>1</sub>	Ao	Control		rrent and duration setting.
0	1		1	2012	B <sub>5</sub>	-		1000	-	B <sub>0</sub>	P-00-Blackery	A[7:0] -> Soft s	tart setting for Phase1
200	1 22			B <sub>6</sub>	0-	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	-		= 8B	h [POR]
0	1		1	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	C <sub>3</sub>	C <sub>2</sub>	C <sub>1</sub>	C <sub>0</sub>			tart setting for Phase2 h [POR]
0	1		0	0	D <sub>5</sub>	D <sub>4</sub>	<b>D</b> <sub>3</sub>	D <sub>2</sub>	D <sub>1</sub>	Do			tart setting for Phase3
													n [POR]
												D[7:0] -> Durati = 0FI	h [POR]
													iption of each byte:
												water and the feet	[6:0] / C[6:0]: Driving Strength
												Bit[6:4]	Selection
												000	1(Weakest)
												001	2
												010	3
												011	4
												100	5
												101	6
												110	7
												111	8(Strongest)
												Bit[3:0]	Min Off Time Setting of GDR [ Time unit ]
												0000	The state of the s
												0011	NA
												0100	2.6
												0101	3.2
												0110	3.9
												0111	4.6
												1000	5.4
												1001	6.3
												1010	7.3
												1011	8.4
												1100	9.8
												1101	11.5
												1110	13.8
												1111	16.5
												3.1.1.1.	10.0
												D[5:4]: d D[3:2]: d	uration setting of phase Juration setting of phase 3 Juration setting of phase 2 Juration setting of phase 1
												Bit[1:0]	Duration of Phase
												00	[Approximation] 10ms
												01	20ms
												10	30ms
												11	40ms
		-						J					
)	0	10	0	0	0	1	0	0	0		Deep Sleep mode		p mode Control:
)	1		0	0	0	0	0	0	A <sub>1</sub>	Ao			Description News INC.
													Normal Mode [POR]
													Enter Deep Sleep Mode 1
													Enter Deep Sleep Mode 2
												enter Deep keep outpu Remark: To Exit Dee	ommand initiated, the chip we sleep Mode, BUSY pad will thigh.  Be Sleep mode, User require VRESET to the driver



Com	man	d Ta	ble									
R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	11	0	0	0	1	0	0	0	1	Data Entry mode setting	Define data entry sequence
0	1		0	0	0	0	0	A2	At	Ao		A[2:0] = 011 [POR]  A [1:0] = ID[1:0] Address automatic increment / decrement setting The setting of incrementing or decrementing of the address counter can be made independently in each upper and lower bit of the address. 00 –Y decrement, X decrement, 01 –Y decrement, X increment, 10 –Y increment, X increment [POR]  A[2] = AM Set the direction in which the address counter is updated automatically after data are written to the RAM. AM= 0, the address counter is updated in the X direction. [POR] AM = 1, the address counter is updated in the Y direction.
0	0	12	0	0	0	1	0	0	1	0	SW RESET	It resets the commands and parameters to their S/W Reset default values except R10h-Deep Sleep Mode  During operation, BUSY pad will output high.  Note: RAM are unaffected by this command.
0	0	14	0	0	0	1	0	1	0	0	HV Ready Detection	HV ready detection A[7:0] = 00h [POR] The command required CLKEN=1 and ANALOGEN=1. Refer to Register 0x22 for detail. After this command initiated, HV Ready detection starts. BUSY pad will output high during detection. The detection result can be read from the Status Bit Read (Command 0x2F).
0	1		0	A <sub>6</sub>	A <sub>5</sub>	A4	0	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>		A[6:4]=n for cool down duration: 10ms x (n+1) A[2:0]=m for number of Cool Down Loop to detect. The max HV ready duration is 10ms x (n+1) x (m) HV ready detection will be trigger after each cool down time. The detection will be completed when HV is ready. For 1 shot HV ready detection, A[7:0] can be set as 00h.



	man D/C#	-	-	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	15	0	0	0	1	0	1	0	1	VCI Detection	VCI Detection
0	1	13	0	0	0	0	0	A <sub>2</sub>	A <sub>1</sub>	Ao	VOI Detection	A[2:0] = 100 [POR] , Detect level at 2.3V
												A[2:0] : VCI level Detect
												A[2:0] VCI level
												011 2.2V
												100 2.3V
												101 2.4V
												110 2.5V
												111 2.6V
												Other NA
												The command required CLKEN=1 and ANALOGEN=1 Refer to Register 0x22 for detail.  After this command initiated, VCI detection starts. BUSY pad will output high during detection. The detection result can be read from the Status Bit Read (Command 0x2F).
0	0	18	0	0	0	1	1	0	0	0	Temperature Sensor	Temperature Sensor Selection
0	1		A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A4	Аз	A <sub>2</sub>	A <sub>1</sub>	Ao	Control	A[7:0] = 48h [POR], external
												temperatrure sensor A[7:0] = 80h Internal temperature sensor
0	0	1A	0	0	0	1	1	0	1	0	Temperature Sensor	Write to temperature register.
0	1		A7	<b>A</b> 6	<b>A</b> 5	A4	Аз	A2	A <sub>1</sub>	Ao	Control (Write to temperature register)	A[7:0] = 7Fh [POR]
0	0	1B	0	0	0	1	1	0	1	1	Temperature Sensor	Read from temperature register.
1	1		A7	A <sub>6</sub>	<b>A</b> 5	A4	Аз	A <sub>2</sub>	A <sub>1</sub>	Ao	Control (Read from temperature register)	
0	0	1C	0	0	0	1	1	1	0	0	Temperature Sensor	Write Command to External temperature
0	1	CALC:	A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A4	<b>A</b> <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	Ao	Control (Write Command	sensor.
0	1	- 3	B <sub>7</sub>	B <sub>6</sub>	B5	B <sub>4</sub>	Вз	B <sub>2</sub>	Bı	Во	to External temperature	A[7:0] = 00h [POR],
0	1		C <sub>7</sub>	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	C <sub>3</sub>	C <sub>2</sub>	C <sub>1</sub>	C <sub>0</sub>	sensor)	B[7:0] = 00h [POR],
							3	02				C[7:0] = 00h [POR],  A[7:6]  A[7:6]  A[7:6]  A[7:6]  Address + pointer  01  Address + pointer + 1st parameter  10  Address + pointer + 1st parameter + 2nd pointer  11  Address  A[5:0] - Pointer Setting  B[7:0] - 1st parameter  C[7:0] - 2nd parameter  The command required CLKEN=1.  Refer to Register 0x22 for detail.  After this command initiated, Write  Command to external temperature  sensor starts. BUSY pad will output high
												during operation.
0	0	1F	0	0	0	1	1	1	1	1	IC revision Read	Read IC revision [POR 0x0D]
1	1		A <sub>7</sub>	A <sub>6</sub>	A5	A4	<b>A</b> <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>		

2.7 inch Series



	man D/C#		D7	D6	D5	D4	D3	D2	D1	DO	Command	Description	
	-	-			-			-			C		
0	0	20	0	0	1	0	0	0	0	0	Master Activation	Activate Display Update Sequence located at R22h.  BUSY pad will output high durit operation. User should not inte operation to avoid corruption of images.	Option is
0	0	21	0	0	1	0	0	0	0	1	Display Update Control	RAM content option for Display	Update
0	1		A <sub>7</sub>	A <sub>6</sub>	<b>A</b> 5	A <sub>4</sub>	Аз	A2	A <sub>1</sub>	Ao	1	A[7:0] = 00h [POR] B[7:0] = 00h [POR]	
0	1		B <sub>7</sub>	0	0	0	0	0	0	0		A[7:4] Red RAM option	
												0000 Normal	
												0100 Bypass RAM cor	
												1000 Inverse RAM cor	ntent
												A[3:0] BW RAM option	
												0000 Normal	
												0100 Bypass RAM cor	ntent as 0
												1000 Inverse RAM cor	ntent
												B[7] Source Output Mode  0 Available Source from S	0 to S175
												1 Available Source from S	And in case of the last of the
0	0	24	0	0	1	0	0	1	0	0	Write RAM (Black White) / RAM 0x24	After this command, data entrie written into the BW RAM until a	
												command is written. Address padvance accordingly	ointers wi
												For Write pixel: Content of Write RAM(BW) = For Black pixel: Content of Write RAM(BW) =	



	D/C#	d Ta	D7	D6	D5	D4	D3	D2	D1	DO	Command	Description	
0	0	22	0	0	1	0	0	0	1	0	Display Update	Display Update Sequence Option:	
0	1		A <sub>7</sub>	<b>A</b> <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	Control 2	Enable the stage for Master Activated A[7:0]= FFh (POR)	tion
												Operating seguence	rameter n Hex)
												Enable clock signal	80
												Disable clock signal	01
												Enable clock signal  → Enable Analog	C0
												Disable Analog	00
												→ Disable clock signal	03
												Enable clock signal  → Load LUT with DISPLAY Mode 1  → Disable clock signal	91
												Enable clock signal  → Load LUT with DISPLAY Mode 2  → Disable clock signal	99
												Enable clock signal  → Load temperature value  → Load LUT with DISPLAY Mode 1  → Disable clock signal	В1
												Enable clock signal  → Load temperature value  → Load LUT with DISPLAY Mode 2  → Disable clock signal	В9
												Enable clock signal  → Enable Analog  → Display with DISPLAY Mode 1  → Disable Analog  → Disable OSC	C7
												Enable clock signal  → Enable Analog  → Display with DISPLAY Mode 2  → Disable Analog  → Disable OSC	CF
												Enable clock signal  → Enable Analog  → Load temperature value  → DISPLAY with DISPLAY Mode 1  → Disable Analog  → Disable OSC	F7
												Enable clock signal → Enable Analog → Load temperature value → DISPLAY with DISPLAY Mode 2 → Disable Analog → Disable OSC	FF
0	0	26	0	0	1	0	0	1	1	0	Write RAM (RED) / RAM 0x26	After this command, data entries w written into the RED RAM until and command is written. Address point advance accordingly.	ther
	k(s );			2	( )		10					For Red pixel: Content of Write RAM(RED) = 1 For non-Red pixel [Black or White] Content of Write RAM(RED) = 0	:
0	0	27	0	0	1	0	0	1	1	1	Read RAM	After this command, data read on t MCU bus will fetch data from RAM According to parameter of Register to select reading RAM0x24/ RAM0 until another command is written. Address pointers will advance accordingly.  The 1st byte of data read is dummy	41h x26,



Comi		-		122	Harris I	22020		200	1000	2372		l	<b>*</b>		
R/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Descript	ion		
0	0	28	0	0	1	0	1	0	0	0	VCOM Sense	for durate VCOM votes the sen register. The contact ANALOG Refer to	tion defined value. sed VCOM nmand requ GEN=1 Register 0 ad will outp	I in 29h b I voltage uired CLh x22 for d	
- 1									-			la			
0	0	29	0	0	1	0	1	0	0	1	VCOM Sense Duration				ring VCOM
0	1		0	1	0	0	A <sub>3</sub>	A2	A <sub>1</sub>	Ao		A[3:0] =	mode and 9h, duratio sense durat	n = 10s.	3:0]+1) sec
0	0	2A	0	0	1	0	1	0	1	0	Program VCOM OTP	Program	VCOM re	gister into	OTP
												Refer to	nmand requ Register 0 ad will outp n.	x22 for d	etail.
0	0	2C	0	0	1	0	1	1	0	0	Write VCOM register	Write VC	COM registe	er from M	ICU interface
0	1		<b>A</b> 7	A <sub>6</sub>	<b>A</b> 5	<b>A</b> 4	Аз	A <sub>2</sub>	A <sub>1</sub>	Ao		A[7:0] =	00h [POR]		
												A[7:0]	VCOM	A[7:0]	VCOM
												08h	-0.2	44h	-1.7
												0Ch	-0.3	48h	-1.8
												10h	-0.4	4Ch	-1.9
												14h	-0.5	50h	-2
												18h	-0.6	54h	-2.1
												1Ch	-0.7	58h	-2.2
												20h	-0.8	5Ch	-2.3
												24h	-0.9	60h	-2.4
												28h	-1	64h	-2.5
												2Ch	-1.1	68h	-2.6
												30h	-1.2	6Ch	-2.7
												34h	-1.3	70h	-2.8
												38h	-1.4	74h	-2.9
												3Ch	-1.5	78h	-3
											1	40h	-1.6	Other	NA



	man			l second	Inguardi.	130000	l'assault	III Carrie	i de la constantina	5799	E	
9:51	D/C#		D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	2D	0 A7	0 A6	1 A5	0 A4	1 A3	1 A2	0 A <sub>1</sub>	1 Ao	OTP Register Read for Display Option	Read Register for Display Option:
1	1		B <sub>7</sub>	B <sub>6</sub>	B <sub>5</sub>	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	Bo		A[7:0]: VCOM OTP Selection
1	1	=	C <sub>7</sub>	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	C <sub>3</sub>	C <sub>2</sub>	C <sub>1</sub>	Co	_	(Command 0x37, Byte A)
1	1	-	D <sub>7</sub>	D <sub>6</sub>	D <sub>5</sub>	D <sub>4</sub>	D <sub>3</sub>	D <sub>2</sub>	D <sub>1</sub>	D <sub>0</sub>	-	B[7:0]: VCOM Register
1	1		E <sub>7</sub>	E <sub>6</sub>	E <sub>5</sub>	E <sub>4</sub>	E <sub>3</sub>	E <sub>2</sub>	E <sub>1</sub>	E <sub>0</sub>	-	(Command 0x2C)
1	1		F <sub>7</sub>	F <sub>6</sub>	F <sub>5</sub>	F <sub>4</sub>	F <sub>3</sub>	F <sub>2</sub>	F <sub>1</sub>	Fo	-	
1	1	-	G <sub>7</sub>	G <sub>6</sub>	G <sub>5</sub>	G <sub>4</sub>	G <sub>3</sub>	G <sub>2</sub>	G <sub>1</sub>	Go	-	C[7:0]~G[7:0]: Display Mode (Command 0x37, Byte B to Byte F)
1	1	-	H <sub>7</sub>	H <sub>6</sub>	H <sub>5</sub>	H <sub>4</sub>	H <sub>3</sub>	H <sub>2</sub>	H <sub>1</sub>	H <sub>0</sub>	-	[5 bytes]
1	1		17	16	15	14	l <sub>3</sub>	12	l <sub>1</sub>	lo	-	Example of the control of the contro
1	1		J <sub>7</sub>	J <sub>6</sub>	J <sub>5</sub>	J <sub>4</sub>	J <sub>3</sub>	J <sub>2</sub>	J <sub>1</sub>	J <sub>0</sub>	-	H[7:0]~K[7:0]: Waveform Version
1	1		K <sub>7</sub>	K <sub>6</sub>	K <sub>5</sub>	K <sub>4</sub>	K <sub>3</sub>	K <sub>2</sub>	K <sub>1</sub>	K <sub>0</sub>	-	(Command 0x37, Byte G to Byte J) [4 bytes]
			N7	<b>N</b> 6	<b>N</b> 5	N4	N3	<b>N</b> 2	N1	N <sub>0</sub>	<del>(</del> 6	[4 Dytes]
0	0	2E	0	0	1	0	1	1	1	0	User ID Read	Read 10 Byte User ID stored in OTP:
1	1		A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A4	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	Ao	and the state of t	A[7:0]]~J[7:0]: UserID (R38, Byte A and
1	1		B <sub>7</sub>	B <sub>6</sub>	B <sub>5</sub>	B <sub>4</sub>	Вз	B <sub>2</sub>	B <sub>1</sub>	B <sub>0</sub>		Byte J) [10 bytes]
1	1		C <sub>7</sub>	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	C <sub>3</sub>	C <sub>2</sub>	C <sub>1</sub>	Co	-	
1	1		D <sub>7</sub>	D <sub>6</sub>	D <sub>5</sub>	D <sub>4</sub>	D <sub>3</sub>	D <sub>2</sub>	D <sub>1</sub>	D <sub>0</sub>		
1	1		E <sub>7</sub>	E <sub>6</sub>	E <sub>5</sub>	E <sub>4</sub>	E <sub>3</sub>	E <sub>2</sub>	E <sub>1</sub>	E <sub>0</sub>	1	
1	1		F <sub>7</sub>	F <sub>6</sub>	F <sub>5</sub>	F <sub>4</sub>	F <sub>3</sub>	F <sub>2</sub>	F <sub>1</sub>	Fo		
1	1		G <sub>7</sub>	G <sub>6</sub>	G <sub>5</sub>	G <sub>4</sub>	G <sub>3</sub>	G <sub>2</sub>	G <sub>1</sub>	Go		
1	1		H <sub>7</sub>	H <sub>6</sub>	H <sub>5</sub>	H <sub>4</sub>	Нз	H <sub>2</sub>	H <sub>1</sub>	Ho		
1	1	3 3	17	l <sub>6</sub>	15	14	l <sub>3</sub>	12	l <sub>1</sub>	lo	-	
1	1		J <sub>7</sub>	J <sub>6</sub>	<b>J</b> <sub>5</sub>	<b>J</b> <sub>4</sub>	J <sub>3</sub>	J <sub>2</sub>	J <sub>1</sub>	Jo	-	
0	0	2F	0	0	1	0	1	1	1	1	Status Bit Read	Read IC status Bit [POR 0x01]
1	1		0	0	As	A4	0	0	Aı	Ao		A[5]: HV Ready Detection flag [POR=0] 0: Ready 1: Not Ready A[4]: VCI Detection flag [POR=0] 0: Normal 1: VCI lower than the Detect level A[3]: [POR=0] A[2]: Busy flag [POR=0] 0: Normal 1: BUSY A[1:0]: Chip ID [POR=01]  Remark: A[5] and A[4] status are not valid after RESET, they need to be initiated by command 0x14 and command 0x15 respectively.
0	0	30	0	0	1	1	0	0	0	0	Program WS OTP	Program OTP of Waveform Setting The contents should be written into RAN before sending this command.  The command required CLKEN=1. Refer to Register 0x22 for detail. BUSY pad will output high during operation.



	man	-			1						T.	
/W#	D/C#	Hex	D7	D6	D5	D4	D3	D2	D1	D0	Command	Description
0	0	31	0	0	1	1	0	0	0	1	Load WS OTP	Load OTP of Waveform Setting  The command required CLKEN=1. Refer to Register 0x22 for detail.  BUSY pad will output high during operation.
0	0	32	0	0	1	1	0	0	1	0	Write LUT register	Write LUT register from MCU interface
0	1	32	201	17.5	300			A <sub>2</sub>	- 10		Write LOT register	[227 bytes], which contains the content of
0	1	5 5	A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	A <sub>3</sub>	B <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>		VS[nX-LUTm], TP[nX], RP[n], SR[nXY],
0	1	3 3	D/	D6	77.500	D4	1559(00)	57.000	Wite and	0.000		FR and XON[nXY]
57750	1		399	-	:						-	Refer to Session 6.7 WAVEFORM SETTING
0			(30)		99%			\$9	*	(99)		SETTING
0	0	34	0	0	1	1	0	1	0	0	CRC calculation	CRC calculation command For details, please refer to SSD1680A application note.  BUSY pad will output high during operation.
0	0	35	0	0	1	1	0	1	0	1	CRC Status Read	CRC Status Read
1	1		A <sub>15</sub>	A <sub>14</sub>	A <sub>13</sub>	A <sub>12</sub>	A11	A <sub>10</sub>	A9	A <sub>8</sub>	and the second	A[15:0] is the CRC read out value
1	1		A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	Аз	A <sub>2</sub>	A <sub>1</sub>	Ao		
0	0	36	0	0	1	1	0	1	1	0	Program OTP selection	Program OTP Selection according to the OTP Selection Control [R37h and R38h]  The command required CLKEN=1. Refer to Register 0x22 for detail. BUSY pad will output high during operation.
0	0	37	0	0	1	1	0	1	1	1	Write Pegister for Display	Write Register for Display Option
0	1	31	A <sub>7</sub>	0	0	0	0	0	1-121-1	0	Option	A[7] Spare VCOM OTP selection
0	1	- 1	B <sub>7</sub>	B <sub>6</sub>	B <sub>5</sub>	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	Bo	111	0: Default [POR]
0	1		C7	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	C <sub>3</sub>	C <sub>2</sub>	C <sub>1</sub>	Co		1: Spare
0	1	-	D <sub>7</sub>	D <sub>6</sub>	D <sub>5</sub>	D <sub>4</sub>	D <sub>3</sub>	D <sub>2</sub>	D <sub>1</sub>	D <sub>0</sub>		B[7:0] Display Mode for WS[7:0]
0	1		E <sub>7</sub>	E <sub>6</sub>	E <sub>5</sub>	E <sub>4</sub>	E <sub>3</sub>	E <sub>2</sub>	E <sub>1</sub>	E <sub>0</sub>		C[7:0] Display Mode for WS[15:8]
0	1		0	F <sub>6</sub>	0	0	F <sub>3</sub>	F <sub>2</sub>	F <sub>1</sub>	Fo		D[7:0] Display Mode for WS[23:16]
0	1		G <sub>7</sub>	G <sub>6</sub>	G <sub>5</sub>	G <sub>4</sub>	G <sub>3</sub>	G <sub>2</sub>	G <sub>1</sub>	Go	-	0: Display Mode 1 1: Display Mode 2
0	1	-	H <sub>7</sub>	H <sub>6</sub>	H <sub>5</sub>	H <sub>4</sub>	H <sub>3</sub>	H <sub>2</sub>	H <sub>1</sub>	Ho	,	1. Display Wode 2
0	1		17	16	15	14	13	12	lı.	lo		F[6]: Ping-Pong for Display Mode 2
0	1		J <sub>7</sub>	J <sub>6</sub>	J <sub>5</sub>	J <sub>4</sub>	J <sub>3</sub>	J <sub>2</sub>	J <sub>1</sub>	Jo		O: RAM Ping-Pong disable [POR]  1: RAM Ping-Pong enable  G[7:0]~J[7:0] module ID /waveform version.  Remarks:  1) A[7:0]~J[7:0] can be stored in OTP  2) RAM Ping-Pong function is not suppor for Display Mode 1



R/W#	D/C#	d Ta		D6	D5	D4	D3	D2	D1	D0	Command	Description	Ň.	
0	0	38	0	0	1	1	1	0	0	0	Write Register for User ID		1 10	
0	1	30	A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	Ao	Write Register for Oser ID		:0]: UserID [10 bytes]	
6.6.47	300		10000	177-1763		Part of the last		None and		1000000		1		
0	1		B <sub>7</sub>	B <sub>6</sub>	B <sub>5</sub>	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	B <sub>0</sub>	-		[7:0]~J[7:0] can be stored in	
0	1		C <sub>7</sub>	C <sub>6</sub>	C <sub>5</sub>	C <sub>4</sub>	C <sub>3</sub>	C <sub>2</sub>	C <sub>1</sub>	Co		OTP		
0	1		D <sub>7</sub>	D <sub>6</sub>	D <sub>5</sub>	D <sub>4</sub>	D <sub>3</sub>	D <sub>2</sub>	D <sub>1</sub>	D <sub>0</sub>				
0	1		E <sub>7</sub>	E <sub>6</sub>	E <sub>5</sub>	E <sub>4</sub>	E <sub>3</sub>	E <sub>2</sub>	E <sub>1</sub>	Eo				
0	1		F <sub>7</sub>	F <sub>6</sub>	F <sub>5</sub>	F <sub>4</sub>	F <sub>3</sub>	F <sub>2</sub>	F <sub>1</sub>	Fo				
0	1		G <sub>7</sub>	G <sub>6</sub>	G <sub>5</sub>	G <sub>4</sub>	G <sub>3</sub>	G <sub>2</sub>	G <sub>1</sub>	G <sub>0</sub>				
0	1		H <sub>7</sub>	H <sub>6</sub>	H <sub>5</sub>	H <sub>4</sub>	Нз	H <sub>2</sub>	H <sub>1</sub>	Ho				
0	1		17	16	15	14	l <sub>3</sub>	12	l <sub>1</sub>	lo				
0	1		J <sub>7</sub>	J <sub>6</sub>	J <sub>5</sub>	J <sub>4</sub>	J <sub>3</sub>	J <sub>2</sub>	J <sub>1</sub>	Jo				
U		_	3/	<b>J</b> 6	<b>J</b> 5	J4	<b>J</b> 3	J2	Ji	30				
0	0	39	0	0	1	1	1	0	0	1	OTP program mode	OTP progra		
0	1		0	0	0	0	0	0	A <sub>1</sub>	Ao		A[1:0] = 00: Normal Mode [POR]		
							==			==350			Internal generated OTP	
												programmin	g voltage	
												· User is rea	uired to EXACTLY follow the	
													ode sequences	
0	0	3C	0	0	1	1	1	1	0	0	Border Waveform Control	Select borde	er waveform for VBD	
0	1		A7	A <sub>6</sub>	<b>A</b> 5	A4	0	0	A <sub>1</sub>	Ao		A[7:0] = C0h	[POR], set VBD as HIZ.	
×			775 - 250		****	55500		97788	\$1657.1	103.1100			ect VBD option	
												A[7:6]	Select VBD as	
												00	GS Transition,	
												04	Defined in A[2] and A[1:0]	
												01	Fix Level, Defined in A[5:4]	
												10	VCOM	
												11[POR]	HiZ	
													evel Setting for VBD	
												A[5:4]	VBD level	
												00	VSS	
												01	VSH1	
												10 11	VSL VSH2	
												11	VSHZ	
												A [1:0] GS T	ransition setting for VBD	
												VBD Level S		
													; 01b: VSH1;	
												10b: VSL; 1		
												A[1:0]	VBD Transition	
												00	LUT0 LUT1	
												10	LUT2	
												11	LUT3	
												I—	T. T. T.	
0	0	3F	0	0	1	1	1	1	1	1	End Option (EOPT)	Option for LI	UT end	
0	1		A7	A <sub>6</sub>	A5	A4	Аз	A <sub>2</sub>	A <sub>1</sub>	Ao	20 N W	Data bytes s	should be set for this	
						100							programmed into Waveform	
												setting.	Wat	
												22h Norr 07h Sou	nal. rce output level keep	
- 1							n II				1	II LIVO I SOU	CE OUIDUI IEVELKEED	



M	D/C#	d Ta		D6	D5	D4	D3	D2	D1	DO	Command	Descripti	on			
0	0	41	0	1	0	0	0	0	0	1	Read RAM Option					
0	1	41	0	0	0	0	0	0	0	Ao	read RAIN Option	A[0]= 0 [F 0 : Read RAM0x24	Read RAM corresponding to			
100 I			\$20			1 10023				X 820	I Description	I	1 101 101	52 B320	55.536	
0	0	44	0	1	0	0	0	1	0	0	Set RAM X - address Start / End position		ne start/en ddress in			
0	1		0	0	A <sub>5</sub>	A <sub>4</sub>	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	Otart / End position		unit for RA		Clion by a	
0	1		0	0	B <sub>5</sub>	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	B <sub>0</sub>		A[5:0]: XSA[5:0], XStart, POR = 00h B[5:0]: XEA[5:0], XEnd, POR = 15h				
0	0	45	0	1	0	0	0	1	0	1	Set Ram Y- address	Specify the start/end positions of				
0	1		A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	Start / End position	window address in the Y direction by address unit for RAM  A[8:0]: YSA[8:0], YStart, POR = 000h				
0	1	-	0	0	0	0	0	0	0	A <sub>8</sub>					25%5	
0	1	-	B <sub>7</sub>	B <sub>6</sub>	B <sub>5</sub>	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	Bo	-				2 - 000h	
0	1		0	0	0	0	0	0	0	B <sub>8</sub>	-		EA[8:0], YE			
	G . ()										L	-		**************************************	AND TO STREET	
0	0	46	0 A <sub>7</sub>	1 A6	0 A <sub>5</sub>	0 A4	0	1 A <sub>2</sub>	A <sub>1</sub>	0 Ao	Auto Write RED RAM for Regular Pattern	Auto Write RED RAM for Regular Patte A[7:0] = 00h [POR]  A[7]: The 1st step value, POR = 0 A[6:4]: Step Height, POR= 000 Step of alter RAM in Y-direction according to Gate				
												A[6:4]	Height	A[6:4]	Height	
												000	8	100	128	
												001	16	101	256	
												010	32	110	296	
												011	64	111	NA	
												Step of al	ep Width, ter RAM ir to Source	X-directi		
												A[2:0]	Width	A[2:0]	Width	
												000	8	100	128	
												001	16	101	176	
												010	32	110	NA	
												011	64	111	NA	
												BUSY par	d will outpo	ut high du	ring	



R/W#	D/C#	Hex	<b>D</b> 7	D6	D5	D4	D3	D2	D1	D0	Command	Descripti	on				
0	0	47	0	1	0	0	0	1	1	1	Auto Write B/W RAM for	Auto Write	e B/W RAI	M for Reg	ular Patter		
0	1		A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A4	0	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	Regular Pattern	A[7:0] = 00h [POR]					
												A[6:4]: Step of al	A[7]: The 1st step value, POR = 0 A[6:4]: Step Height, POR= 000 Step of alter RAM in Y-direction according to Gate				
												A[6:4]	Height	A[6:4]	Height		
												000	8	100	128		
												001	16	101	256		
												010	32	110	296		
												011	64	111	NA		
			A[2:0] 000	to Source Width 8	A[2:0] 100	Width 128											
												000	8		128		
												001	16	101	176		
												010	32	110	NA		
												011	64	111	NA		
			,									During op high.	eration, B	USY pad	will output		
0	0	4E	0	1	0	0	1	1	1	0	Set RAM X address	Make initi	al settings	for the R	AM X		
0	1	Meet.	0	0	<b>A</b> 5	<b>A</b> 4	Аз	<b>A</b> 2	Aı	Ao	counter		n the addr				
0	0	4F	0	1	0	0	1	1	1	1	Set RAM Y address	Make initi	al settings	for the R	AM Y		
0	1		<b>A</b> 7	A6	A <sub>5</sub>	A4	Аз	A2	Aı	Ao	counter	address in	n the addr	ess count			
0	1		0	0	0	0	0	0	0	A <sub>8</sub>		A[8:0]: 00	0h [POR].				
					0 10		02		va c		dii						
0	0	7F	0	1	1	1	1	1	1	1	NOP	does not l module. However	it can be u emory Wri	effect on to	he display minate		

WINSTAR Display 26/39 2.7 inch Series



### 8. Optical Specifications

Measurements are made with that the illumination is under an angle of 45 degree, the detection is perpendicular unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ.	Max	Units	Notes
R	White Reflectivity	White	30	35	-	%	8-1
CR	Contrast Ratio	Indoor	8:1		-		8-2
GN	2Grey Level	-		DS+(WS-DS)*n(m-1)			8-3
T update	Image update time	at 25 °C		3	-	sec	
Life		Topr		1000000times or 5years			

#### **Notes:**

- 8-1. Luminance meter: Eye-One Pro Spectrophotometer.
- 8-2. CR=Surface Reflectance with all white pixel/Surface Reflectance with all black pixels.
- 8-3 WS: White state, DS: Dark state



### 9. Handling, Safety and Environment Requirements

#### Warning

The display glass may break when it is dropped or bumped on a hard surface. Handle with care. Should the display break, do not touch the electrophoretic material. In case of contact with electrophoretic material, wash with water and soap.

#### Caution

The display module should not be exposed to harmful gases, such as acid and alkali gases, which corrode electronic components. Disassembling the display module.

Disassembling the display module can cause permanent damage and invalidates the warranty agreements.

Observe general precautions that are common to handling delicate electronic components. The glass can break and front surfaces can easily be damaged. Moreover the display is sensitive to static electricity and other rough environmental conditions.

	Data sheet status
Product specification	This data sheet contains final product specifications.
	Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC

134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

WINSTAR Display 28/39 2.7 inch Series



### 10.Reliability test

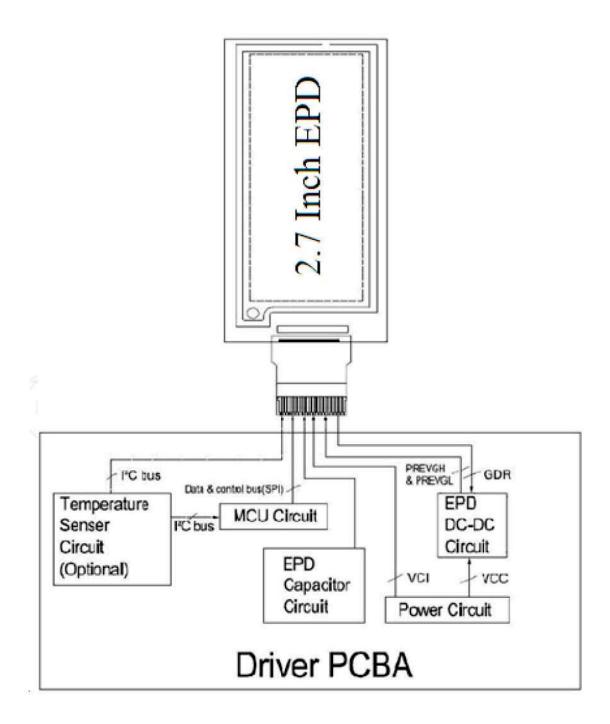
NO	Test items	Test condition
1	Low-Temperature Storage	T = -25°C, 240 h Test in white pattern
2	High-Temperature Storage	T=70°C, RH=40%, 240h Test in white pattern
3	High-Temperature Operation	T=50°C, RH=35%, 240h
4	Low-Temperature Operation	0°C, 240h
5	High-Temperature, High-Humidity Operation	T=40°C, RH=80%, 240h
6	High Temperature, High Humidity Storage	T=50°C, RH=80%, 240h Test in white pattern
7	Temperature Cycle	1 cycle:[-25° C 30min]→[+70 ° C 30 min] : 50 cycles Test in white pattern
8	UV exposure Resistance	765W/m² for 168hrs,40 °C Test in white pattern
9	ESD Gun	Air+/-15KV;Contact+/-8KV (Test finished product shell, not display only) Air+/-8KV;Contact+/-6KV (Naked EPD display, no including IC and FPC area) Air+/-4KV;Contact+/-2KV (Naked EPD display, including IC and FPC area)

#### Note:

Put in normal temperature for 1hour after test finished, display performance is ok.



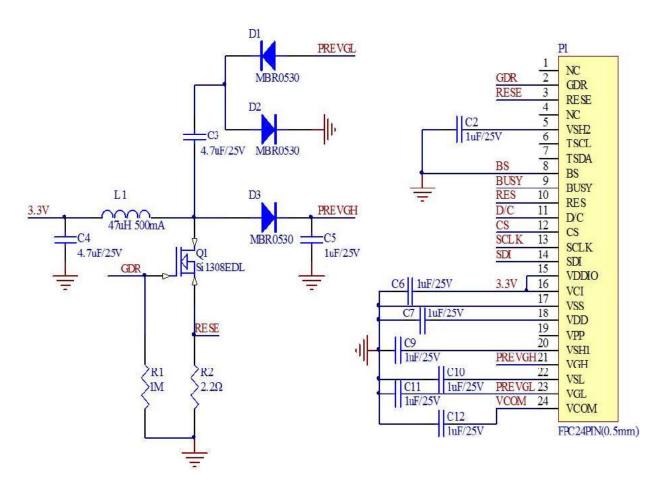
### 11. Block Diagram



WINSTAR Display 30/39 2.7 inch Series



#### 12. Reference Circuit



Part Name	Requirements for spare part		
C1—C12	0603/0805; X5R/X7R;Voltage Rating:≥25V		
R1、R2 0603/0805;1% variation,≥0.05W			
D1—D3	MBR0530: 1)Reverse DC Voltage≥30V 2)Io≥500mA		
D1—D3	3)Forward voltage ≤430mV		
01	Si1308EDL:1)Drain-Source breakdown voltage≥30V		
Q1	2)Vgs(th)≤1.5V 3)Rds(on)≤400mΩ		
L1	refer to NR3015: Io=500mA(max)		
P1	24pins,0.5mm pitch		



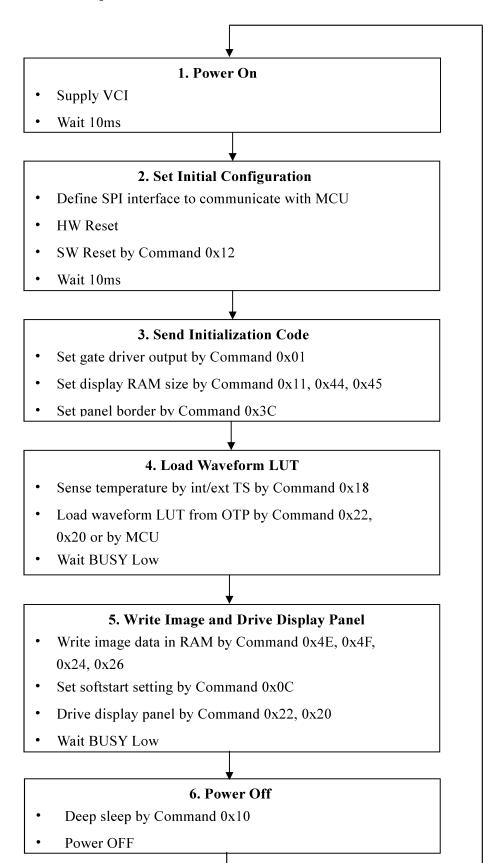
### 13. Matched Development Kit

Our Development Kit designed for SPI E-paper Display aims to help users to learn how to use E-paper Display more easily. It can refresh black-white E-paper Display and three-color (black, white and red/Yellow) WINSTAR Display 's E-paper Display. And it is also added the functions of USB serial port, Raspberry Pi and LED indicator light ect. DESPI Development Kit consists of the development board and the pinboard.



### 14. Typical Operating Sequence

### 14.1 Normal Operation Flow





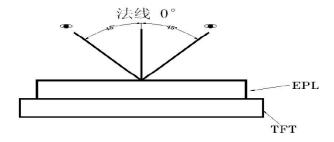
# 15.Inspection condition 15.1 Environment

Temperature:  $25\pm3^{\circ}$ C Humidity:  $55\pm10^{\circ}$ RH

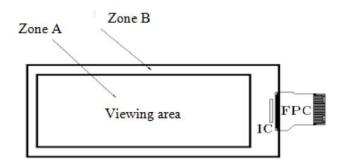
#### 15.2 Illuminance

 $Brightness: 1200 {\sim} 1500 LUX; distance: 20-30 CM; Angle: Relate~30° surround.$ 

### 15.3 Inspection method



### 15.4 Display area





### 15.5 Inspection standard

### 15.5.1 Electric inspection standard

NO.	Item	Standard	Defect level	Method	Scope	
1	Display	Display complete Display uniform	MA			
2	Black/White spots	D<0.25mm Allowed		Visual inspection		
3	Black/White spots (No switch)	L $\leq$ 0.6mm, W $\leq$ 0.2mm, N $\leq$ 1 L $\leq$ 2.0mm,W $>$ 0.2mm, Not Allow L $>$ 0.6mm, Not Allow		Visual/ Inspection card	Zone A	
4	Ghost image	Allowed in switching process	MI	Visual inspection		
5	Flash spots/ Larger FPL size	Flash spots in switching, Allowed FPL size larger than viewing area, Allowed	MI	Visual/ Inspection card	Zone A Zone B	
6	Display wrong/Missing	All appointed displays are showed correct	MA	Visual inspection	Zone A	
7	Short circuit/ Circuit break/ Display abnormal	Not Allow		1.5		



### 15.5.2 Appearance inspection standard

NO.	Item	Standard	Defect level	Method	Scope
1	B/W spots /Bubble/ Foreign bodies/ Dents	D= $(L+W)/2$ D $\leq 0.25$ mm, Allowed 0.25mm $\leq D\leq 0.4$ mm, N $\leq 3$ D $\geq 0.4$ mm, Not Allow	MI	Visual inspection	Zone A
2	Glass crack	Not Allow	MA	Visual	Zone A Zone B
3	Dirty	Allowed if can be removed	MI	/ Microscope	Zone A Zone B
4	Chips/Scratch/ Edge crown	$X \le 3$ mm, $Y \le 0.5$ mmAnd without affecting the electrode is permissible $2$ mm $\le X$ or $2$ mm $\le Y$ Not Allow $W \le 0.1$ mm, $L \le 5$ mm, No harm to the electrodes and $N \le 2$ allow	MI	Visual / Microscope	Zone A Zone B
5	TFT Cracks	Not Allow	MA	Visual / Microscope	Zone A Zone B
6	Dirty/ foreign body	Allowed if can be removed/ allow	MI	Visual / Microscope	Zone A / Zone B
7	FPC broken/ Goldfingers exidation/ scratch	Not Allow	MA	Visual / Microscope	Zone B



8	TFT edge bulge /TFT chromatic aberration	TFT edge bulge: X≤3mm, Y≤0.3mm Allowed TFT chromatic aberration :Allowed	MI	Visual / Microscope	Zone A Zone B
9	PCB damaged/ Poor welding/ Curl	PCB (Circuit area) damaged Not Allow PCB Poor welding Not Allow PCB Curl≤1%			
10	Edge glue height/ Edge glue bubble	Edge Adhesives H≤PS surface (Including protect film) Edge adhesives seep in≤1/2 Margin width Length excluding Edge adhesives bubble: bubble Width ≤1/2 Margin width; Length ≤0.5mm₀ n≤5	MI	Visual / Ruler	Zone B
11	Protect film	Surface scratch but not effect protect function, Allowed		Visual Inspection	
12	Silicon glue	Thickness ≤ PS surface(With protect film): Full cover the IC; Shape: The width on the FPC ≤ 0.5mm (Front) The width on the FPC≤1.0mm (Back) smooth surface,No obvious raised.	MI	Visual Inspection	
13	Warp degree (TFT substrate)	t≤2.0mm	MI	Ruler	
14	Color difference in COM area (Silver point area)	Allowed		Visual Inspection	



### 16. Packing

TBD



#### 17. Precautions

- (1) Do not apply pressure to the EPD panel in order to prevent damaging it.
- (2) Do not connect or disconnect the interface connector while the EPD panel is in operation.
- (3) Do not touch IC bonding area. It may scratch TFT lead or damage IC function.
- (4) Please be mindful of moisture to avoid its penetration into the EPD panel, which may cause damage during operation.
- (5) High temperature, high humidity, sunlight or fluorescent light may degrade the EPD panel's performance. Please do not expose the unprotected EPD panel to high temperature, high humidity, sunlight, or fluorescent for long periods of time.